

## Silicon NPN Power Transistors

2SD1550

## DESCRIPTION

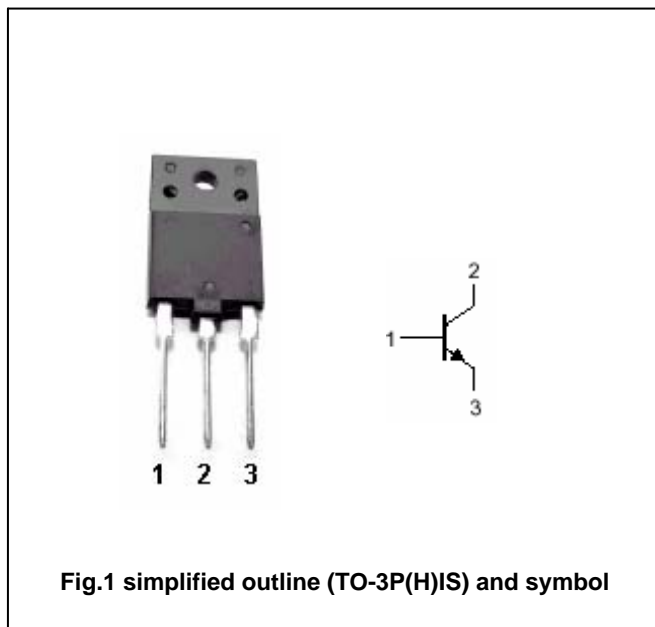
- With TO-3P(H)IS package
- High voltage ,high speed
- Low collector saturation voltage

## APPLICATIONS

- For color TV horizontal deflection output applications

## PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Collector   |
| 3   | Emitter     |



## Absolute maximum ratings (Ta=25°C)

| SYMBOL    | PARAMETER                   | CONDITIONS             | VALUE   | UNIT             |
|-----------|-----------------------------|------------------------|---------|------------------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter           | 1000    | V                |
| $V_{CEO}$ | Collector-emitter voltage   | Open base              | 400     | V                |
| $V_{EBO}$ | Emitter-base voltage        | Open collector         | 5       | V                |
| $I_C$     | Collector current           |                        | 10      | A                |
| $P_C$     | Collector power dissipation | $T_C=25^\circ\text{C}$ | 50      | W                |
| $T_j$     | Junction temperature        |                        | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage temperature         |                        | -55~150 | $^\circ\text{C}$ |

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS                                | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V <sub>CEQ(SUS)</sub> | Collector-emitter sustaining voltage | I <sub>C</sub> =0.1A , I <sub>B</sub> =0  | 400 |      |     | V    |
| V <sub>CEsat</sub>    | Collector-emitter saturation voltage | I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A |     |      | 5.0 | V    |
| V <sub>BEsat</sub>    | Base-emitter saturation voltage      | I <sub>C</sub> =8A ; I <sub>B</sub> =1.6A |     |      | 1.5 | V    |
| I <sub>CBO</sub>      | Collector cut-off current            | V <sub>CB</sub> =800V; I <sub>E</sub> =0  |     |      | 10  | μ A  |
| I <sub>EBO</sub>      | Emitter cut-off current              | V <sub>EB</sub> =5V; I <sub>C</sub> =0    |     |      | 10  | μ A  |
| h <sub>FE-1</sub>     | DC current gain                      | I <sub>C</sub> =1A ; V <sub>CE</sub> =5V  | 8   |      |     |      |
| h <sub>FE-2</sub>     | DC current gain                      | I <sub>C</sub> =8A ; V <sub>CE</sub> =5V  | 5   |      |     |      |

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PACKAGE OUTLINE

